Claims

1. A precious metal article comprising a precious metal base (1) and a transparent film layer (2) directly attached on the surface of the precious metal base (1), the precious metal is gold or silver;
wherein the material of the transparent film layer (2) is an AF pill .

2. The precious metal article of claim 1, wherein the gold has a gold content within a range of 33-99.99 wt%, preferably 75-99.99 wt%; and the silver has a silver content within a range of 92.5-99 wt%;
preferably, the precious metal base (1) has a surface roughness of 0.001-50μm, more preferably 0.005-0.1μm.

3. The precious metal article of claim 1 or 2, wherein the transparent film layer (2) has a thickness of 0.0001-10μm, preferably 0.0005-0.1μm.

4. A method for preparing a precious metal article of any one of claims 1-3 comprising the following step: depositing the transparent film layer (2) directly on the surface of the precious metal base (1) by physical vapor deposition.

5. The method of claim 4, wherein the method further comprises conducting an intra-furnace vacuumization process prior to depositing a

transparent film layer (2) on the surface of the precious metal base (1), wherein the vacuum degree during the intra-furnace vacuumization process is within a range of 1×10^{-2}Pa-7×10^{-3}Pa.

6. The method of claim 4, wherein the physical vapor deposition mode is vacuum evaporation plating, vacuum sputtering coating or vacuum ion plating;

preferably, the physical vapor deposition mode is the vacuum evaporation plating.

7. The method of claim 6, wherein the vacuum evaporation plating mode comprises: adjusting the vacuum degree to 1.8×10^{-2}-2.2×10^{-2}Pa, enabling the intra-furnace environment to be suitable for electroplating, injecting argon gas with an gas flow of 55-65sccm, adjusting the vacuum degree to 1.3×10^{0}-1.7×10^{0}Pa, performing glow cleaning for 170-190s, injecting oxygen gas with an oxygen gas flow rate of 75-85sccm, adjusting the vacuum degree to 3.8×10^{-1}-4.2×10^{-1}Pa, activating the aluminum target and the silicon target and operating for 80-100s and 170-190s respectively, and then shutting off the power sources of the aluminum target and the silicon target, activating the power supply of the evaporation source, setting the silicon target current to be within a range of 2.8-3.2A;

performing evaporation for 170-190s under the condition that the current

of the evaporation source is within a range of 700-740A; further performing evaporation for 170-190s under the condition that the current of the evaporation source is within a range of 750-800A; subsequently performing evaporation for 410-430s under the condition that the current of the evaporation source is within a range of 800-900A; thereby forming a transparent film layer having a thickness within a range of 0.0001-10μm.

8. The method of any one of claims 4-7, wherein the method further comprises cleaning the surface of the precious metal base (1), the cleaning mode is ultrasonically cleaning the surface of the precious metal base (1) for 1-15min under the ultrasonic frequency condition of 20-30kHz, and/or, wiping and cleaning the surface of the precious metal base (1) with a dust-free cloth dipped in 95-98 wt% alcohol.

9. The method of claim 8, wherein the method further comprises a step of baking the ultrasonically treated precious metal base (1), the baking temperature is 100-150°C, and the baking time is 5-30min.